

Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)			Complete if Known		
Sheet	1	of	1	Application Number	Not Yet Assigned 10/780,526
				Filing Date	Herewith
				First Named Inventor	Milan Pophristic
				Art Unit	N/A
				Examiner Name	Not Yet Assigned
				Attorney Docket Number	EMCORE 3.0-084

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	AA	US-2003/0015708-A1	01-23-2003	Parikh, et al.	
	AB	US-2003/0062525-A1	04-03-2003	Parikh, et al.	
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	AD	US-5,158,909-B1	10-27-1992	Ohtsuka, et al.	
	AE	US-5,602,418-B1	02-11-1997	Imai, et al.	
	AF	US-5,789,760-B1	08-04-1998	Iinkawa, et al.	
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	AQ	US-5,399,887-B1	03-21-1995	Weitzel, et al.	
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	AW	US-2003/0006415-A1	01-09-2003	Yokogawa, et al.	

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Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ² -Number ³ -Kind Code ⁴ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²

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Examiner Signature		Date Considered	12/5/05
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Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)			Complete if Known		
			Application Number	10780,526	
			Filing Date	February 17, 2004	
			First Named Inventor	Milan Pophristic	
			Art Unit	2811	
			Examiner Name	Not Yet Assigned	
Sheet	1	of	1	Attorney Docket Number	EMCORE 3.0-084

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		Number-Kind Code ² (if known)			
	AA	US-2003/141518-A1	07-31-2003	Yokogawa et al.	
	AB	US-5,296,395	03-22-1994	Khan et al.	
	AC	US-6,653,215-B1	11-25-2003	Brown et al.	

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
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	BA	EP-1 189 287-A	03-20-2002	Matsushita Electric Industrial Co., Ltd.		
	BB	WO-03/026021-A	03-27-2003	Cree Lighting Company		

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	CA	"High barrier height GaN Schottky diodes: Pt/GaN and Pd/GaN" APPLIED PHYSICS LETTERS, AMERICAN INSTITUTE OF PHYSICS, New York, US, vol. 68 no. 9, 2-26-96; pp. 1267-1269	
	CB	Lin Yow-Jon et al: "Nitrogen-vacancy-related defects and Fermi level pinning in n-GaN Schottky diodes" 8/1/03, JOURNAL OF APPLIED PHYSICS, AMERICAN INSTITUTE OF PHYSICS, New York, US, pp. 1819-1822.	

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